

SILICON
TRANSISTORS

T0-92



ECB

2SB621, A (PNP) & 2SD592, A (NPN) are complementary silicon planar epitaxial transistors designed for AF output amplifiers.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	2SD592	2SD592A
Collector-Emitter Voltage	VCEO	2SB621	2SB621A
Emitter-Base Voltage	VEBO		
Collector Current	IC		
Total Power Dissipation	Ptot		
Operating Junction & Storage Temperature	Tj, Tstg		
		30V	60V
		25V	50V
			5V
			1A
		750mW	
		-55 to +150°C	

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITION
Collector Cutoff Current	ICBO		100	nA	VCB=20V IE=0
Collector-Base Breakdown Voltage	BVCBO	30	60	V	IC=10µA IE=0
Collector-Base Breakdown Voltage		2SB621 / 2SD592			
Collector-Base Breakdown Voltage		2SB621A / 2SD592A			
Collector-Emitter Breakdown Voltage	LVCEO	25	50	V	IC=2mA IB=0
Collector-Emitter Breakdown Voltage		2SB621 / 2SD592			
Collector-Emitter Breakdown Voltage		2SB621A / 2SD592A			
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10µA IC=0
D.C. Current Gain	HFE	85	340		IC=500mA VCE=10V*
D.C. Current Gain		50			IC=1A VCE=10V*
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=500mA IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		1.2	V	IC=500mA IB=50mA*
Current Gain Bandwidth Product	fT	200 TYP		MHz	IC=50mA VCE=10V
Output Capacitance	Cob		30	pF	VCB=10V f=1MHz
Output Capacitance		2SB621, A			
Output Capacitance		2SD592, A	20	pF	

Pulse Test : Pulse Width < 300µs, Duty Cycle < 1%.

HFE Grouping

Q : 85-170

R : 120-240

S : 170-340



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